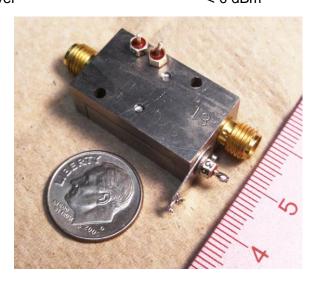
Features

1 to 6 GHz RF Frequency: Gain @ 20K: $36dB \pm 2dB$ Noise temperature @ 20 K: <7K at 1.4 GHz. < 11K to 6 GHz Noise figure @ 20 K: < 0.16 dBNoise figure @ 300K <1.6 dB IRL (-20log | S11 |) > 10 dBORL (-20log | S22 |) > 10 dBOperating temperature: 4.2 K- 320 K DC power @300K 4V, 21mA, 84mW DC power @ 17 K: 3V, 12mA, 36 mW Output power for 1 dB compression -3 dBm Safe input power level < 0 dBm



Description

The CITLF1 a SiGe low noise amplifier intended for extremely low noise cryogenic applications. The amplifier utilizes resistive feedback to achieve good input match (S11) and high gain stability. The amplifier is optimum for the frequency range 1 to 6 GHz.

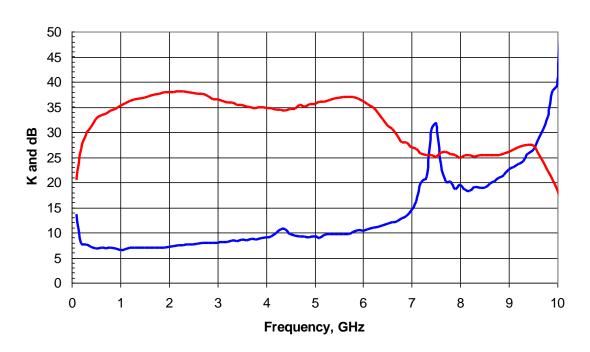
It is powered from a single positive DC supply which is optimum at 3V but can be reduced to as low as 1.1V for low power dissipation. Application of up to 6V wil not damage the amplifier. It is recommended that the power supply for the amplifier be current limited to 100mA. A series resistor may be used. For example 150 ohms to a +5V supply will provide 3V, 13mA when the amplifier is at 20K.

The amplifier offers an optional DC bias tee for an external device connected to the amplifier input. The bias tee is formed by two 20K resistors connected to the input; one can be used as a source of current and one the sense the voltage across the external device. Voltages applied to the bias tee have no effect on amplifier operation.

The amplifier is 20.7mm x 15.9mm x 8.7mm excluding connectors with input SMA at left and output SMA at right as shown above.

Typical Test Results

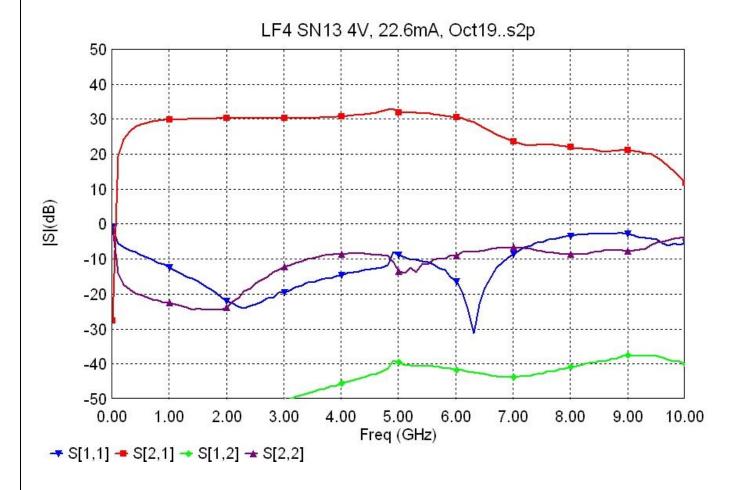
LF4 Noise and Gain at 19K, 3V, 13mA Oct 17, 2009



LF4 Noise and Gain at 300K, 3V Oct 17, 2009



S parameters at 300K



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